

NJT4030P, NJV4030PT1G, NJV4030PT3G

Bipolar Power Transistors

PNP Silicon

Features

- Collector –Emitter Sustaining Voltage –
 $V_{CE(sus)} = 40 \text{ Vdc (Min) @ } I_C = 10 \text{ mAdc}$
- High DC Current Gain –
 $h_{FE} = 200 \text{ (Min) @ } I_C = 1.0 \text{ Adc}$
 $= 100 \text{ (Min) @ } I_C = 3.0 \text{ Adc}$
- Low Collector –Emitter Saturation Voltage –
 $V_{CE(sat)} = 0.200 \text{ Vdc (Max) @ } I_C = 1.0 \text{ Adc}$
 $= 0.500 \text{ Vdc (Max) @ } I_C = 3.0 \text{ Adc}$
- SOT-223 Surface Mount Packaging
- Epoxy Meets UL 94, V-0 @ 0.125 in
- ESD Ratings:
 - ♦ Human Body Model, 3B; > 8000 V
 - ♦ Machine Model, C; > 400 V
- AEC-Q101 Qualified and PPAP Capable
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*



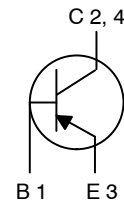
ON Semiconductor®

<http://onsemi.com>

PNP TRANSISTOR 3.0 AMPERES 40 VOLTS, 2.0 WATTS

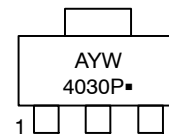


**SOT-223
CASE 318E
STYLE 1**



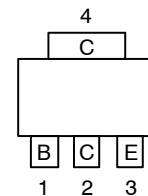
Schematic

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
4030P = Specific Device Code
■ = Pb-Free Package

PIN ASSIGNMENT



Top View Pinout

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NJT4030P, NJV4030PT1G, NJV4030PT3G

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	40	Vdc
Collector–Base Voltage	V _{CB}	40	Vdc
Emitter–Base Voltage	V _{EB}	6.0	Vdc
Base Current – Continuous	I _B	1.0	Adc
Collector Current Continuous Peak	I _C	3.0 5.0	Adc
Total Power Dissipation Total P _D @ T _A = 25°C mounted on 1" sq. (645 sq. mm) Collector pad on FR–4 bd material Total P _D @ T _A = 25°C mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR–4 bd material	P _D	2.0 0.80	W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	–55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case Junction–to–Ambient on 1" sq. (645 sq. mm) Collector pad on FR–4 bd material Junction–to–Ambient on 0.012" sq. (7.6 sq. mm) Collector pad on FR–4 bd material	R _{θJA} R _{θJA}	64 155	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T _L	260	°C

ORDERING INFORMATION

Device	Package	Shipping [†]
NJT4030PT1G	SOT–223 (Pb–Free)	1,000 / Tape & Reel
NJV4030PT1G	SOT–223 (Pb–Free)	1,000 / Tape & Reel
NJT4030PT3G	SOT–223 (Pb–Free)	4,000 / Tape & Reel
NJV4030PT3G	SOT–223 (Pb–Free)	4,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NJT4030P, NJV4030PT1G, NJV4030PT3G

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (I _C = 10 mAdc, I _B = 0 Adc)	V _{CEO(sus)}	40	–	–	Vdc
Emitter-Base Voltage (I _E = 50 µAdc, I _C = 0 Adc)	V _{EBO}	6.0	–	–	Vdc
Collector Cutoff Current (V _{CB} = 40 Vdc)	I _{CBO}	–	–	100	nAdc
Emitter Cutoff Current (V _{BE} = 6.0 Vdc)	I _{EBO}	–	–	100	nAdc

ON CHARACTERISTICS (Note 1)

Collector-Emitter Saturation Voltage (I _C = 0.5 Adc, I _B = 5.0 mAdc) (I _C = 1.0 Adc, I _B = 10 mAdc) (I _C = 3.0 Adc, I _B = 0.3 Adc)	V _{CE(sat)}	– – –	– – –	0.150 0.200 0.500	Vdc
Base-Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 0.1 Adc)	V _{BE(sat)}	–	–	1.0	Vdc
Base-Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 2.0 Vdc)	V _{BE(on)}	–	–	1.0	Vdc
DC Current Gain (I _C = 0.5 Adc, V _{CE} = 1.0 Vdc) (I _C = 1.0 Adc, V _{CE} = 1.0 Vdc) (I _C = 3.0 Adc, V _{CE} = 1.0 Vdc)	h _{FE}	220 200 100	– – –	– 400 –	–

DYNAMIC CHARACTERISTICS

Output Capacitance (V _{CB} = 10 Vdc, f = 1.0 MHz)	C _{ob}	–	40	–	pF
Input Capacitance (V _{EB} = 5.0 Vdc, f = 1.0 MHz)	C _{ib}	–	130	–	pF
Current-Gain – Bandwidth Product (Note 2) (I _C = 500 mA, V _{CE} = 10 V, f _{test} = 1.0 MHz)	f _T	–	160	–	MHz

1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.
2. f_T = |h_{FE}| • f_{test}

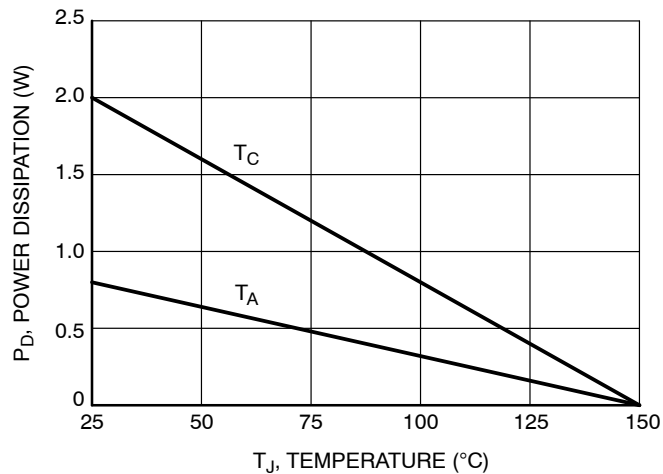


Figure 1. Power Derating

TYPICAL CHARACTERISTICS

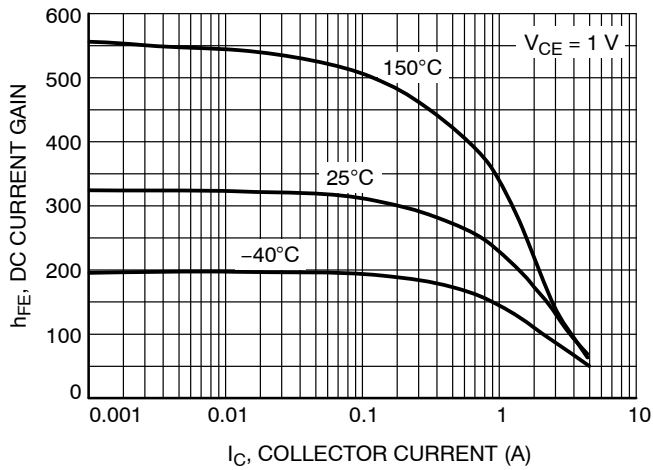


Figure 2. DC Current Gain

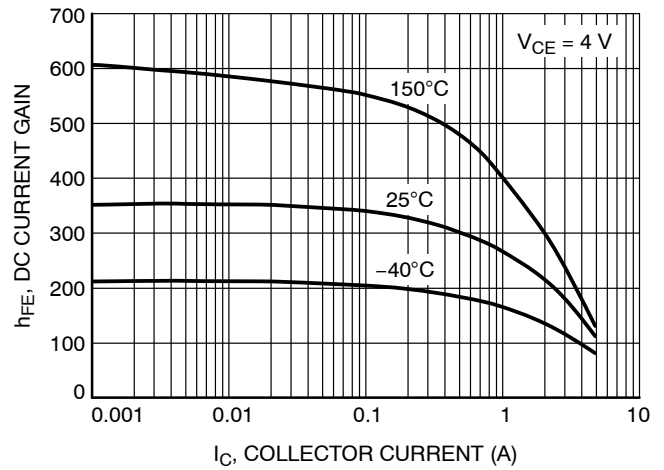


Figure 3. DC Current Gain

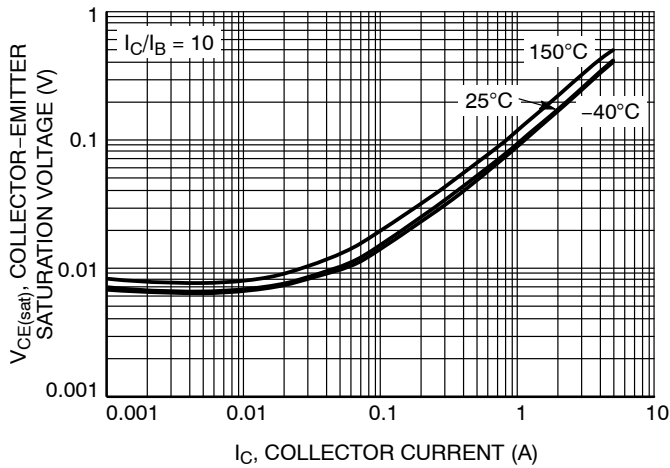


Figure 4. Collector-Emitter Saturation Voltage

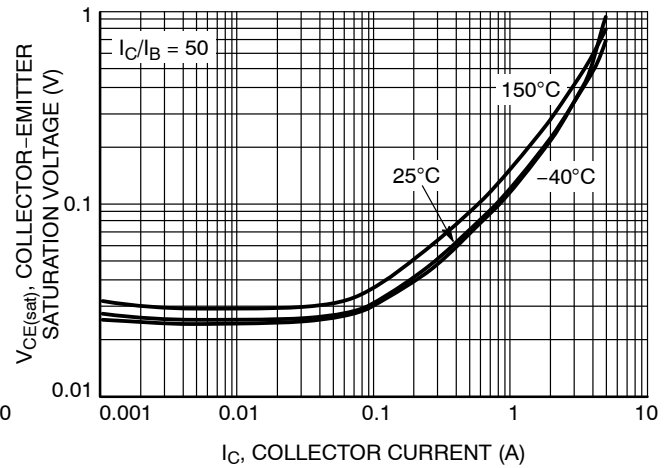


Figure 5. Collector-Emitter Saturation Voltage

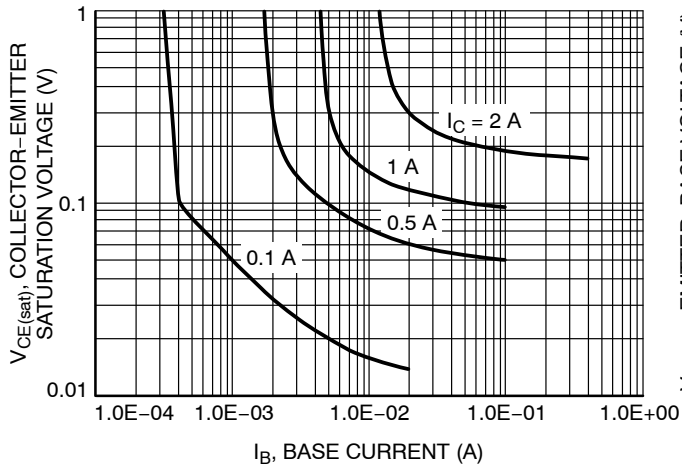


Figure 6. Collector Saturation Region

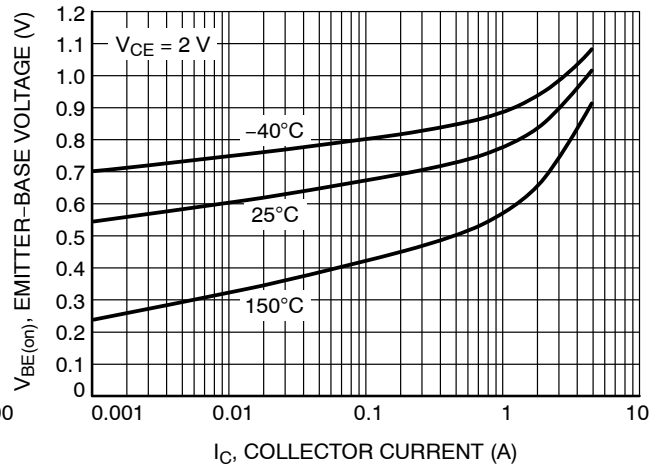


Figure 7. $V_{BE(on)}$ Voltage

TYPICAL CHARACTERISTICS

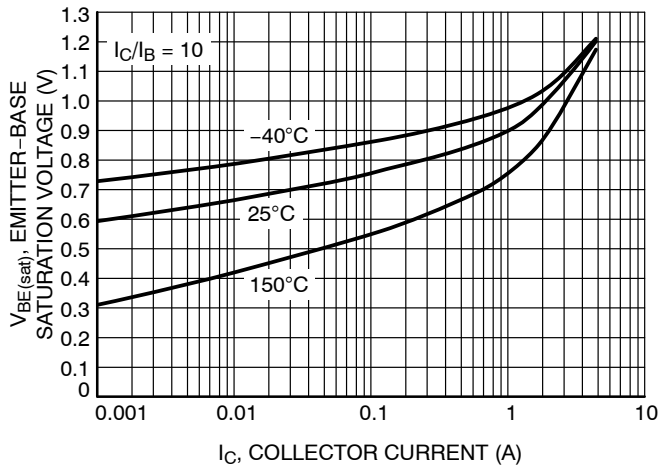


Figure 8. Base-Emitter Saturation Voltage

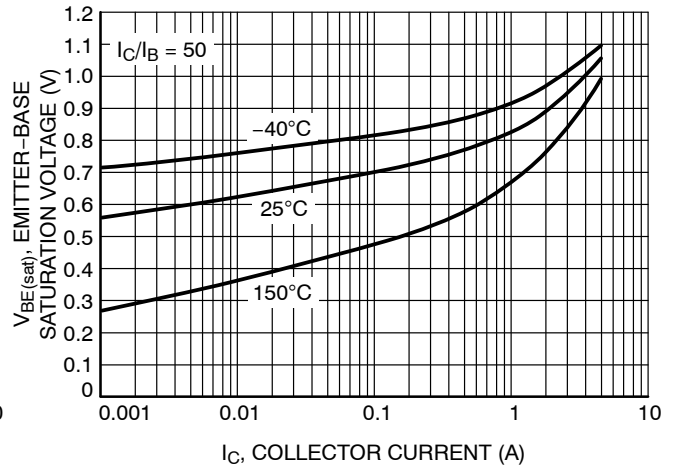


Figure 9. Base-Emitter Saturation Voltage

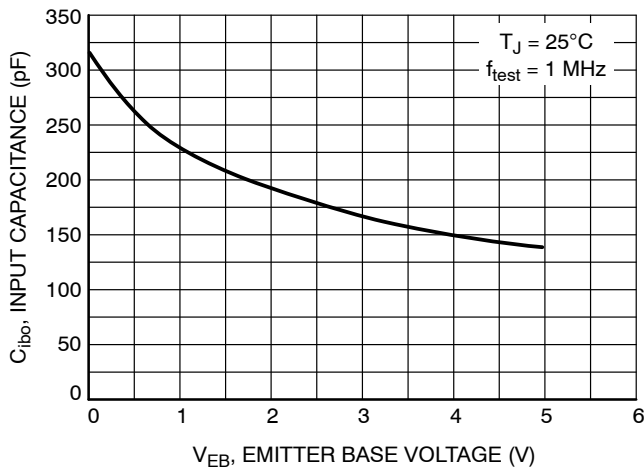


Figure 10. Input Capacitance

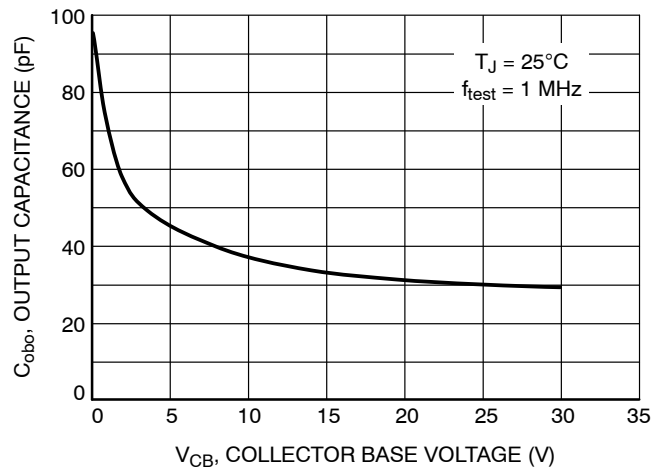


Figure 11. Output Capacitance

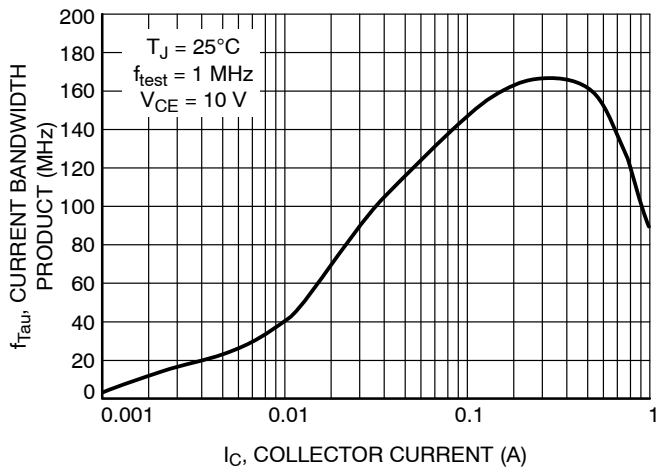


Figure 12. Current-Gain Bandwidth Product

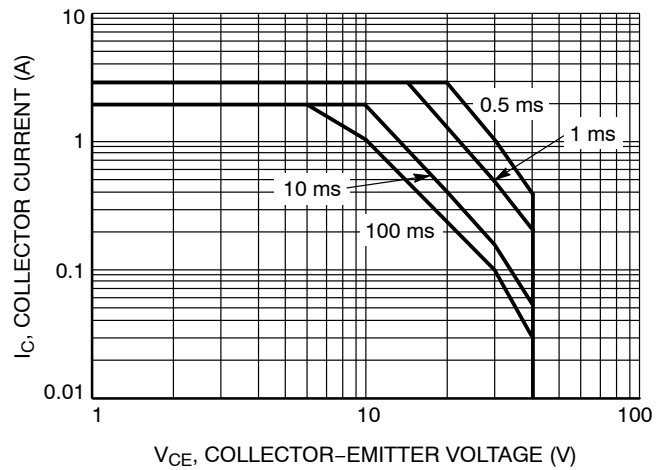
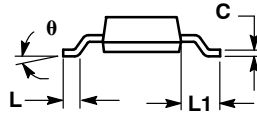
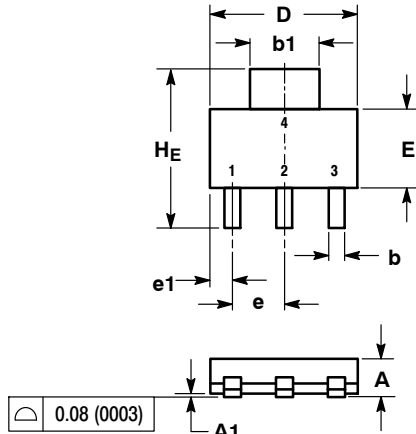


Figure 13. Safe Operating Area

NJT4030P, NJV4030PT1G, NJV4030PT3G

PACKAGE DIMENSIONS

SOT-223 (TO-261)
CASE 318E-04
ISSUE N

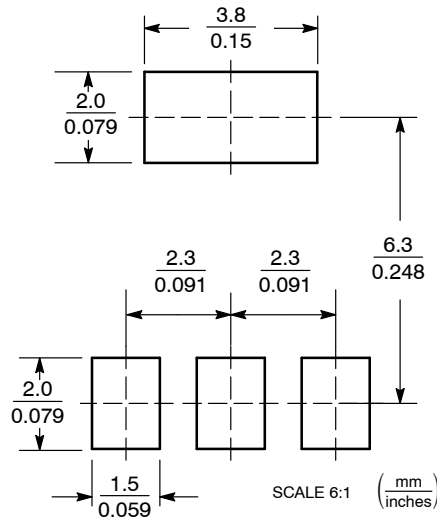


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	---	---	0.008	---	---
L1	1.50	1.75	2.00	0.060	0.069	0.078
H_E	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	—	10°	0°	—	10°

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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